

Current induced light emission and light induced current in molecular tunneling junctions

Michael Galperin^{1,*} and Abraham Nitzan¹

¹*School of Chemistry, Tel Aviv University, Tel Aviv 69978, Israel*

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Abstract

The interaction of metal-molecule-metal junctions with light is considered within a simple generic model. We show, for the first time, that light induced current in unbiased junctions can take place when the bridging molecule is characterized by a strong charge-transfer transition. The same model shows current induced light emission under potential bias that exceeds the molecular excitation energy. Results based on realistic estimates of molecular-lead coupling and molecule-radiation field interaction suggest that both effects should be observable.

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Molecular conduction nano-junctions have been under intense study for some time. A class of molecules not yet investigated in this context are those characterized by strong charge-transfer transitions into their first excited state. The dipole moment of such molecules changes considerably in such transitions[1], expressing a strong shift of the electronic charge distribution. In the independent electron picture, the charge transfer nature of the first excited state implies that either the highest occupied, or the lowest unoccupied, molecular orbitals (LUMO and HOMO) is dominated by atomic orbitals of larger amplitude (and better overlap with metal orbitals) on one side of the molecule than on the other and therefore stronger coupling to one of the leads. We show that when such molecular wire connects between two metal leads with the charge transfer direction approximately parallel to its axis, optical pumping may create an internal driving force for charge flow between the leads. Such optical-resonance activation of current flow is different from previously demonstrated adiabatic pumping[2] and from previously discussed strong field optical control mechanisms[3, 4].

The opposite phenomenon: light emission in current carrying tunnel junctions has already been demonstrated. Emission from bare junction[5] was attributed to surface plasmons[6]. Emission from molecular nanojunctions[7, 8] was not so far discussed theoretically.

Our model provides a simple framework for treating both light induced current and current induced light in molecular junctions. Following its introduction below we present results of self consistent numerical solutions as well as approximate expressions for the corresponding electron and photon fluxes. We examine, using reasonable experimentally-based parameters, the magnitudes of these effects and conclude that both phenomena can be observable under fairly general conditions.

In our model (Fig. 1) the molecule is represented by its HOMO, $|1\rangle$, and LUMO, $|2\rangle$, with energies ε_1 and ε_2 and gap $\varepsilon_{21} = \varepsilon_2 - \varepsilon_1$, positioned between two leads represented by free electron reservoirs L and R characterized by the electronic chemical potentials μ_L and μ_R . $\mu_L - \mu_R = e\Phi$ is the voltage bias. In the independent electron picture molecular excitation corresponds to transfer

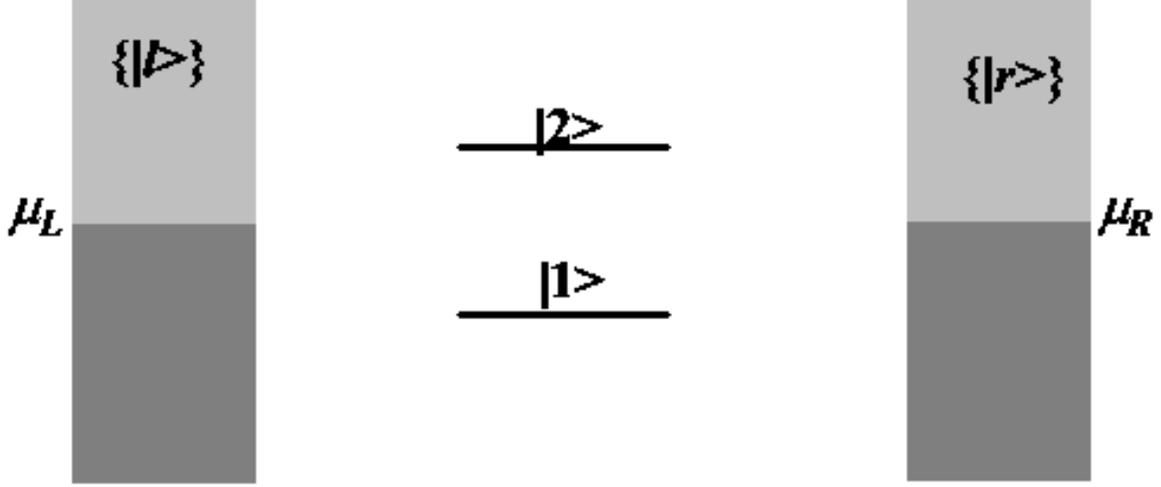


FIG. 1: The molecular junction model. The right ($R = \{|r \rangle\}$) and left ($L = \{|l \rangle\}$) manifolds represent the leads' electronic states; μ_L and μ_R are the corresponding electrochemical potentials. The molecule is represented by its HOMO and LUMO levels.

of an electron between levels $|1 \rangle$ and $|2 \rangle$. The corresponding Hamiltonian is

$$\hat{H} = \hat{H}_0 + \hat{V}_M + \hat{V}_N + \hat{V}_P = \hat{H}_J + \hat{V}_N + \hat{V}_P \quad (1)$$

$$\hat{H}_0 = \sum_{m=1,2} \varepsilon_m \hat{c}_m^\dagger \hat{c}_m + \sum_{k \in \{L,R\}} \varepsilon_k \hat{c}_k^\dagger \hat{c}_k + \hbar \sum_{\alpha} \omega_{\alpha} \hat{a}_{\alpha}^\dagger \hat{a}_{\alpha} \quad (2)$$

$$\hat{V}_M = \sum_{K=L,R} \sum_{m=1,2; k \in K} \left(V_{km}^{(MK)} \hat{c}_k^\dagger \hat{c}_m + \text{H.c.} \right) \quad (3)$$

$$\hat{V}_N = \sum_{K=L,R} \sum_{k \neq k' \in K} \left(V_{kk'(NK)} \hat{c}_k^\dagger \hat{c}_{k'} \hat{c}_2^\dagger \hat{c}_1 + \text{H.c.} \right) \quad (4)$$

$$\hat{V}_P = \begin{cases} \left(V_0^{(P)} \hat{a}_0 \hat{c}_2^\dagger \hat{c}_1 + \text{H.c.} \right) & \text{case a} \\ \sum_{\alpha} \left(V_{\alpha}^{(P)} \hat{a}_{\alpha} \hat{c}_2^\dagger \hat{c}_1 + \text{H.c.} \right) & \text{case b} \end{cases} \quad (5)$$

where H.c. denotes Hermitian conjugate. \hat{H}_0 in (2) contains additively terms that correspond to the isolated molecule, the free leads and the radiation field. Eqs. (3)-(5) describe the coupling between these subsystems. The operators \hat{c} (\hat{c}^\dagger) and \hat{a} (\hat{a}^\dagger) are annihilation (creation) operators for electrons and photons. \hat{V}_M is the standard electron transfer coupling that gives rise to net current

in the biased junction and \hat{V}_N describes energy transfer between the molecule and electron-hole excitations in the leads. The latter interaction strongly affects the lifetime of excited molecules near metal surfaces and should be included in any analysis of phenomena involving resonance radiation and molecular conduction junctions. The molecule-radiation field coupling \hat{V}_P , Eq. (5), will be taken in two forms: The form (5a) describes driving of the junction by the electromagnetic field mode $\alpha = 0$, Eq. (5b) is used when addressing the issue of spontaneous light emission from current carrying junctions. We limit ourselves to near resonance processes pertaining to linear spectroscopy. This justifies the use of the rotating wave approximation (RWA) in Eq. (5). Note that the radiative coupling coefficients reflect properties of the local electromagnetic field at the molecular bridge which depend on the metallic boundary conditions.

In the Keldysh non-equilibrium Green function approach the steady state currents through the bridge are obtained from

$$I_B = \int_{-\infty}^{+\infty} \frac{dE}{2\pi\hbar} \text{Tr} [\Sigma_B^<(E)\mathbf{G}^>(E) - \Sigma_B^>(E)\mathbf{G}^<(E)] \quad (6)$$

were the Green functions (GFs) G and the self energies (SEs) Σ are defined in the bridge subspace. The subscript B corresponds to a particular relaxation processes represented by the SE $\Sigma_B^<,>$. At steady state the absorption and emission photon fluxes, I_{abs} and I_{em} , the non radiative relaxation flux, I_N , and the source-drain current, I_{sd} , come into balance. The SEs needed for their evaluation are calculated as sums of independent contributions associated with the different relaxation processes (the non-crossing approximation)

$$\Sigma = \Sigma_{ML} + \Sigma_{MR} + \Sigma_P + \Sigma_{NL} + \Sigma_{NR} \quad (7)$$

where Σ_X ($X = ML, MR, P, NL, NR$) is the SE associated with the coupling $V^{(X)}$ in Eqs. (3)-(5).

On the Keldysh contour these SEs are 2×2 matrices in the bridge space

$$\Sigma_{MK,mm'}(\tau_1, \tau_2) = \sum_{k \in K} V_{mk}^{(MK)} g_k(\tau_1, \tau_2) V_{km'}^{(MK)} \quad (8)$$

$$\begin{aligned} \Sigma_{NK,mm'}(\tau_1, \tau_2) &= \delta_{mm'} \sum_{k \neq k' \in K} \left| V_{kk'}^{(NK)} \right|^2 \\ &\times g_k(\tau_2, \tau_1) g_{k'}(\tau_1, \tau_2) G_{\bar{m}\bar{m}}(\tau_1, \tau_2) \end{aligned} \quad (9)$$

$$\begin{aligned} \Sigma_P(\tau_1, \tau_2) &= i \sum_{\alpha} \left| V_{\alpha}^{(P)} \right|^2 \\ &\times \begin{bmatrix} F_{\alpha}(\tau_2, \tau_1) G_{22}(\tau_1, \tau_2) & 0 \\ 0 & F_{\alpha}(\tau_1, \tau_2) G_{11}(\tau_1, \tau_2) \end{bmatrix} \end{aligned} \quad (10)$$

here and below $K = L, R$ denotes the left and right leads, $m, m' = 1, 2$ and $\bar{m} = 2\delta_{m,1} + \delta_{m,2}$. g_k and F_α are free electron and photon GFs in state k and mode α , respectively. The retarded/advanced, lesser and greater projections of these SEs on the real time axis are obtained using the Langreth formulas and can be expressed at steady state situations in energy space. In the wide-band approximation and assuming that the HOMO and LUMO are not mixed by their interactions with the leads, the SEs associated with electron exchange between molecule and leads have the familiar forms

$$\Sigma_{MK,mm'}^r = [\Sigma_{MK,m'm}^a]^* = -i\delta_{mm'}\Gamma_{MK,m}/2 \quad (11a)$$

$$\Sigma_{MK,mm'}^< = i\delta_{mm'}f_K(E)\Gamma_{MK,m} \quad (11b)$$

$$\Sigma_{MK,mm'}^> = -i\delta_{mm'}[1 - f_K(E)]\Gamma_{MK,m} \quad (11c)$$

$$\Gamma_{MK,m} = 2\pi \sum_{k \in K} \left| V_{km}^{(MK)} \right|^2 \delta(E - \varepsilon_k) \quad (11d)$$

$$f_K(E) = [\exp \{ (E - \mu_K)/k_B T \} + 1]^{-1} \quad (11e)$$

The SEs associated with the non-radiative and radiative energy relaxation processes are similarly obtained in the forms

$$\Sigma_{NK,mm'}^<(E) = \delta_{mm'} \int \frac{d\omega}{2\pi} B_{NK}(\omega, \mu_K) G_{\bar{m}\bar{m}}^<(E + \omega) \quad (12a)$$

$$\Sigma_{NK,mm'}^>(E) = \delta_{mm'} \int \frac{d\omega}{2\pi} B_{NK}(\omega, \mu_K) G_{\bar{m}\bar{m}}^>(E - \omega) \quad (12b)$$

$$B_{NK}(\omega, \mu_K) = \int \frac{dE}{2\pi} C_{NK}(E, \omega) f_K(E) [1 - f_K(E + \omega)] \quad (12c)$$

$$C_{NK}(E, \omega) = (2\pi)^2 \sum_{k \neq k' \in K} \left| V_{kk'}^{(NK)} \right|^2 \times \delta(E - \varepsilon_k) \delta(E + \omega - \varepsilon_{k'}) \quad (12d)$$

and

$$\Sigma_{\mathbf{P}}^<(E) = \sum_{\alpha} \left| V_{\alpha}^{(P)} \right|^2 \quad (13a)$$

$$\times \begin{bmatrix} (1 + N_{\alpha})G_{22}^<(E + \omega_{\alpha}) & 0 \\ 0 & N_{\alpha}G_{11}^<(E - \omega_{\alpha}) \end{bmatrix}$$

$$\Sigma_{\mathbf{P}}^>(E) = \sum_{\alpha} \left| V_{\alpha}^{(P)} \right|^2 \quad (13b)$$

$$\times \begin{bmatrix} N_{\alpha}G_{22}^>(E + \omega_{\alpha}) & 0 \\ 0 & (1 + N_{\alpha})G_{11}^>(E - \omega_{\alpha}) \end{bmatrix}$$

where N_α is the number of photons in mode α . The corresponding retarded and advanced SEs are more difficult to calculate from the Langreth rules. For simplicity we assume, in the spirit of the wide band approximation, that all diagonal components of Σ are purely imaginary. Consequently

$$\Sigma^{\mathbf{r}}(E) = [\Sigma^{\mathbf{a}}(E)]^\dagger = \frac{[\Sigma^>(E) - \Sigma^<(E)]}{2} \equiv -\frac{i}{2}\Gamma \quad (14)$$

We use (14) to get the retarded and advanced GFs according to $G_{mm'}^{\mathbf{r}}(E) = (G_{m'm}^{\mathbf{a}}(E))^* = [E - \varepsilon_m - \Sigma_{mm}^{\mathbf{r}}(E)]^{-1} \delta_{mm'}$. $G^{\langle,\rangle}$ needed in (6) are then obtained from the Keldysh equation $\mathbf{G}^{\langle,\rangle}(E) = \mathbf{G}^{\mathbf{r}}(E)\Sigma^{\langle,\rangle}(E)\mathbf{G}^{\mathbf{a}}(E)$. After evaluating these matrices we can use Eq. (6) with the appropriate self energy to calculate the desired flux. We are particularly interested in I_{em} and I_{sd} .

With regard to the radiative interactions we consider two models:

(A) To study the effect of pumping the junction with light we use a model with a single photon mode of frequency ω_0 and disregard all other modes, as described by Eq. (5a). In the semiclassical limit for the radiation field and in the RWA we can set $N_0 = 1$ and take the coupling $\hat{V}_0^{(P)}$ as a product of the local electric field amplitude and the molecular transition dipole[9]. The charge transfer transition on the bridge is expressed in this model by taking LUMO bridge level more strongly coupled to one lead than to the other. For the HOMO this inequality is assumed weaker or reversed. The flux of interest is I_{sd} under illumination.

(B) To describe current driven spontaneous emission we use the interaction (5b) with all radiation field modes taken in their vacuum state. The frequency resolved emission, $I'_{em}(\omega) = dI_{em}(\omega)/d\omega$ is obtained from (6) using the frequency resolved self energies obtained from (13)

$$\Sigma_{\mathbf{P}}^{\leq}(E, \omega) = \frac{\gamma_P(\omega)}{2\pi\rho_P(\omega)} \begin{bmatrix} G_{22}^{\leq}(E + \omega) & 0 \\ 0 & 0 \end{bmatrix} \quad (15a)$$

$$\Sigma_{\mathbf{P}}^{\geq}(E, \omega) = \frac{\gamma_P(\omega)}{2\pi\rho_P(\omega)} \begin{bmatrix} 0 & 0 \\ 0 & G_{11}^{\geq}(E - \omega) \end{bmatrix} \quad (15b)$$

with the radiative width

$$\gamma_P(\omega) = 2\pi \sum_{\alpha} |V_{\alpha}^{(P)}|^2 \delta(\omega - \omega_{\alpha}) = 2\pi \left| V_{\alpha}^{(P)} \right|_{\omega}^2 \rho_P(\omega) \quad (16)$$

and the density of photon modes, $\rho_P(\omega) = \omega^2/(\pi^2 c^3)$ where c is the speed of light. The total emission flux is found from $I_{em}^{tot} = \int_0^{\infty} d\omega I'_{em}(\omega)$.

In general, the coupled equations for the self energies and the Green functions have to be solved self consistently. The numerical results displayed below were obtained from such an iterative solution. More transparent closed forms may be written under the additional simplifying assumptions:

(a) ε_{21} is large relative to the total widths of levels 1 and 2; (b) $C_{NK}(E, \omega)$; $K = L, R$, Eq. (12d), is taken constant independent of E and ω ; (c) $\gamma_P(\omega)$, Eq. (16), is also assumed constant and (d) keep only the lowest (second) order in the radiative coupling \hat{V}_P . It is then possible to express the relevant self energies and the resulting currents in terms of the electronic populations n_1 and n_2 of levels 1 and 2 using $n_m = (2\pi i)^{-1} \int_{-\infty}^{+\infty} dE G_{mm}^<(E)$, $m = 1, 2$. In addition, for case **(A)** we are interested in the small or no voltage regime, whereupon to a good approximation $n_1 = 1$ and $n_2 = 0$. This leads, for model **(A)**, to

$$I_{sd} = \int \frac{dE}{2\pi\hbar} \sum_{m=1,2} \Gamma_{ML,m} G_{mm}^r(E) \Gamma_{MR,m} G_{mm}^a(E) [f_L(E) - f_R(E)] \quad (17)$$

$$+ \left| V_0^{(P)} \right|^2 \int \frac{dE}{2\pi\hbar} \frac{\Gamma_{ML,1} \Gamma_{MR,2} f_L(E - \omega_0) [1 - f_R(E)] - \Gamma_{ML,2} \Gamma_{MR,1} f_R(E - \omega_0) [1 - f_L(E)]}{[(E - \varepsilon_2)^2 + (\Gamma_2/2)^2] \times [(E - \omega_0 - \varepsilon_1)^2 + (\Gamma_1/2)^2]}$$

The first term on the right is the usual Landauer term that vanishes at zero potential bias, $f_L = f_R$. The second term shows explicitly the effect of pumping. In the absence of bias we get

$$I_{sd} = \left| V_0^{(P)} \right|^2 \int \frac{dE}{2\pi\hbar} \frac{f(E - \omega_0) [1 - f(E)] \{ \Gamma_{ML,1} \Gamma_{MR,2} - \Gamma_{ML,2} \Gamma_{MR,1} \}}{[(E - \varepsilon_2)^2 + (\Gamma_2/2)^2] \times [(E - \omega_0 - \varepsilon_1)^2 + (\Gamma_1/2)^2]} \quad (18)$$

where $f = f_L = f_R$. For our choice of parameters below the analytical results (17) and (18) provide excellent approximations to the full self-consistent calculation. Furthermore, when ω is not too far from its resonance value ε_{21} we can approximate $f(E - \omega_0) [1 - f(E)]$ by 1 to get

$$I_{sd} = \frac{\left| V_0^{(P)} \right|^2}{\hbar} \frac{\Gamma}{(\varepsilon_2 - \omega_0 - \varepsilon_1)^2 + (\Gamma/2)^2} \times \frac{\Gamma_{ML,1} \Gamma_{MR,2} - \Gamma_{ML,2} \Gamma_{MR,1}}{\Gamma_1 \Gamma_2} \quad (19)$$

Eqs. (18) and (19) show explicitly how asymmetry in the HOMO and LUMO couplings to the metal electrodes leads to photocurrent in the present model.

For model **(B)** the frequency resolved emission is obtained from (6) and (15) in the form

$$I'_{em}(\omega) = \frac{\gamma_P(\omega)}{\hbar} \int_{-\infty}^{+\infty} \frac{dE}{2\pi} \left\{ \frac{f_L(E + \omega) \Gamma_{ML,2} + f_R(E + \omega) \Gamma_{MR,2}}{(E + \omega - \varepsilon_2)^2 + (\Gamma_2/2)^2} \times \frac{[1 - f_L(E)] \Gamma_{ML,1} + [1 - f_R(E)] \Gamma_{MR,1}}{(E - \varepsilon_1)^2 + (\Gamma_1/2)^2} \right\} \quad (20)$$

and the integrated emission is obtained, using the same approximations as before, in the anticipated form

$$I_{em}^{tot} = \frac{\gamma_P(\varepsilon_{21})}{\hbar} n_2 (1 - n_1) \quad (21)$$

The level populations n_1 and n_2 should be obtained from the full self consistent calculation. For $\Phi > \varepsilon_{21}$ both LUMO and HOMO bridge levels are well inside the energy window between the leads' chemical potentials. A good approximation for these populations is (written for the case of

negatively biased left electrode) $n_2 = \Gamma_{ML,2}/\Gamma_2$; $n_1 = \Gamma_{ML,1}/\Gamma_1 + n_2(B_N + \gamma_P)/\Gamma_1$. (21) then leads to

$$I_{em}^{tot} = \frac{\gamma_P}{\hbar} \frac{\Gamma_{ML,2}\Gamma_{MR,1}}{\Gamma_1\Gamma_2} \quad (22)$$

Comparing to (18) we see that tailoring the molecule-leads coupling asymmetry such that resonance radiation will induce electron flow in a given direction enhances light emission under such bias that leads to electron current in the opposite direction.

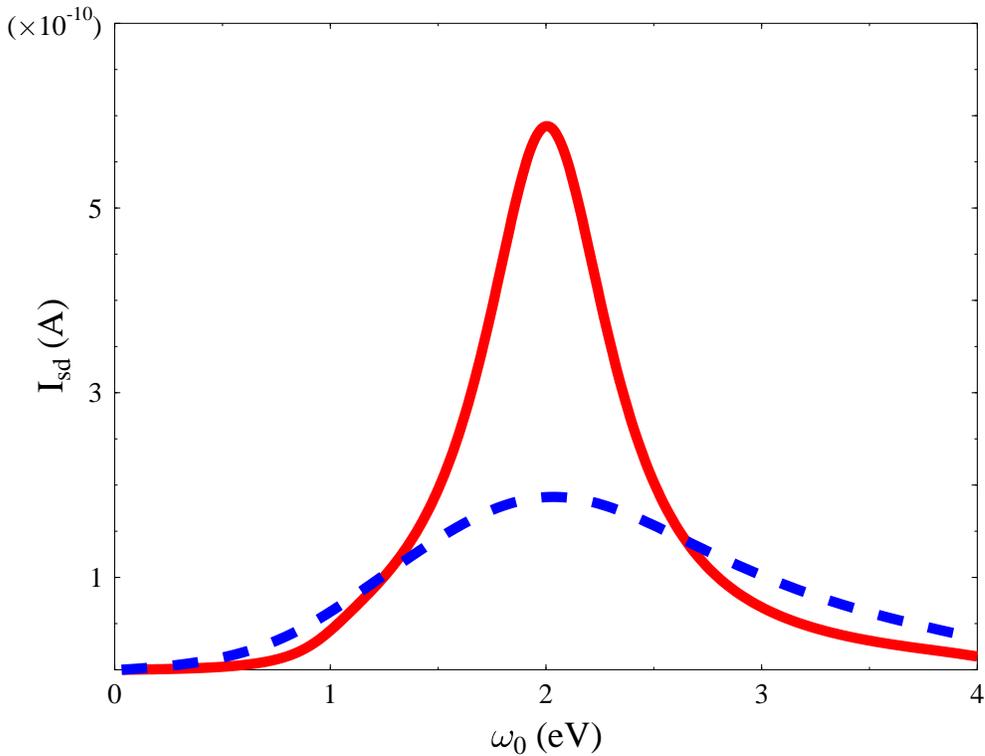


FIG. 2: The light induced current in the model of Fig. 1 in the absence of external potential bias. Full (red) line: $T = 300$ K, $\varepsilon_{21} = 2$ eV, $\Gamma_{ML,1} = \Gamma_{MR,1} = 0.2$ eV, $\Gamma_{ML,2} = 0.02$ eV, $\Gamma_{MR,2} = 0.3$ eV, $\gamma_P = 10^{-6}$ eV, $B_{NL} = B_{NR} = 0.1$ eV and $V_0^{(P)} = 10^{-3}$ eV. Dashed (blue) line — same parameters except $\Gamma_{MK,m} \times 3$ ($m = 1, 2$) is used.

Numerical results obtained from the self consistent calculation are shown in Figs. 2 and 3. Figure 2 shows the light induced current obtained using a set of reasonable junction parameters. In particular, for a molecule with transition dipole moment ~ 1 D the choice $V_0^{(P)} = 10^{-3}$ eV corresponds to an incident field intensity $\sim 10^8$ watt/cm².

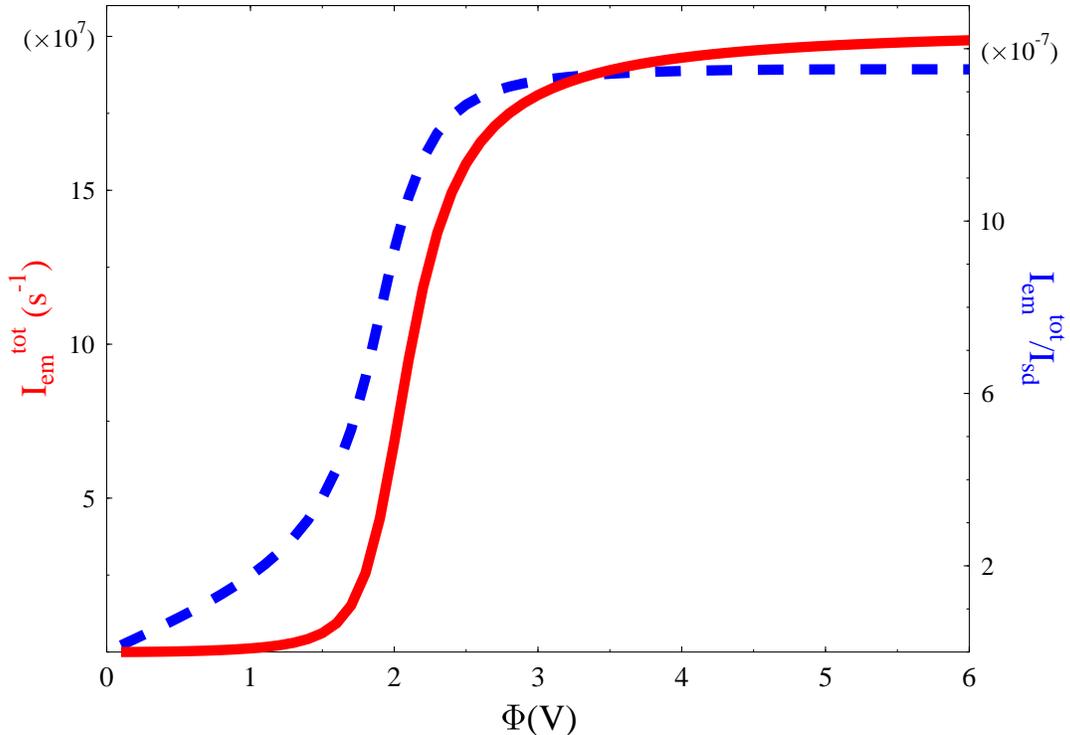


FIG. 3: The integrated photon emission rate (full line, red) and yield (dashed line, blue) plotted against the bias voltage. Parameters are as in Fig. 2 except $\Gamma_{MK,m} = 0.1$ eV, $K = L, R$, $m = 1, 2$.

Fig. 3 shows the integrated emission as well as the predicted photon emission yield. The later is defined as the ratio between the emitted photon current and the electronic current passed by the junction — both displayed as functions of the bias voltage.

These results, obtained under rather conservative choices of damping parameters, indicate that both light induced current and the molecular mechanism (as opposed to the surface plasmon mechanism) for current induced emission in tunnel junctions can lead to measurable signals. This molecular mechanism can in principle be distinguished from the plasmon mechanism for light emission by the frequency dependence of the resolved emission, as implied by Eq. (20).

In conclusion, we have described a model that accounts for observed current induced light emission from molecular tunnel junctions and provides the tools for determining the intensity and yield of such emission as functions of key junction parameters. The same model predict that resonant light induced current can occur in junctions employing molecular bridges with strong

charge-transfer transition to their first excited state. We have concluded, using reasonable parameter, that light driven electronic currents and current driven light emission are realistic possibilities. The linewidths and lineshapes associated with these signal can also be analyzed by the same theoretical framework. Correlating observations with predictions made in this paper should help the interpretation of future experiments in this direction.

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* Present address: Department of Chemistry, Northwestern University, Evanston IL 60208, U.S.A.

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